

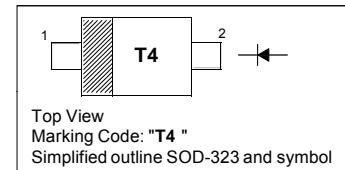
Silicon Epitaxial Planar Switching Diode

Features

- SOD-323 package
- Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



MARKING:T4

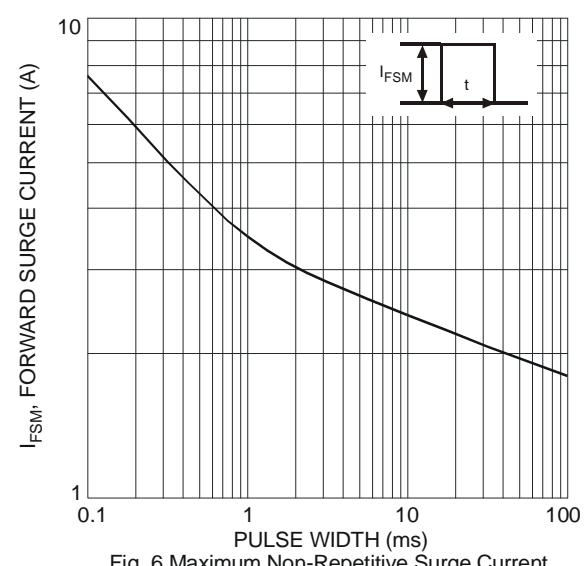
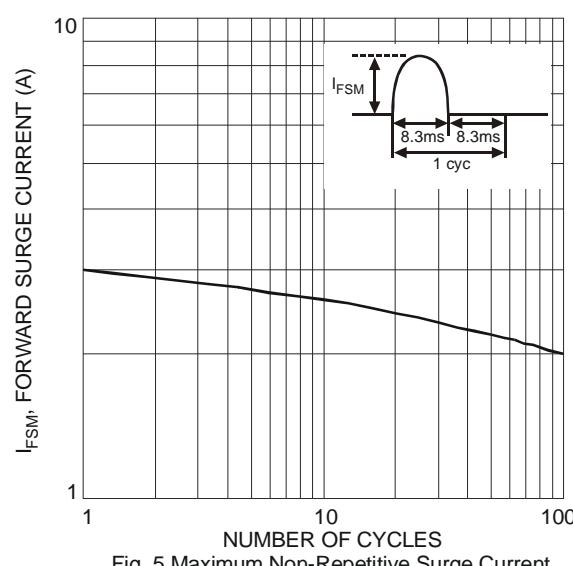
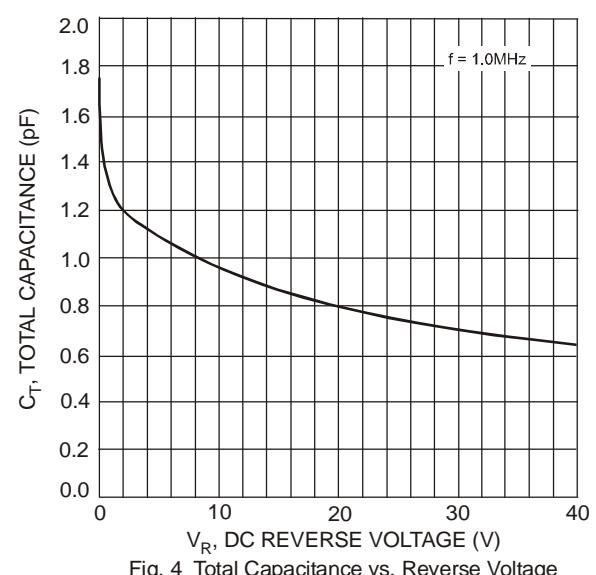
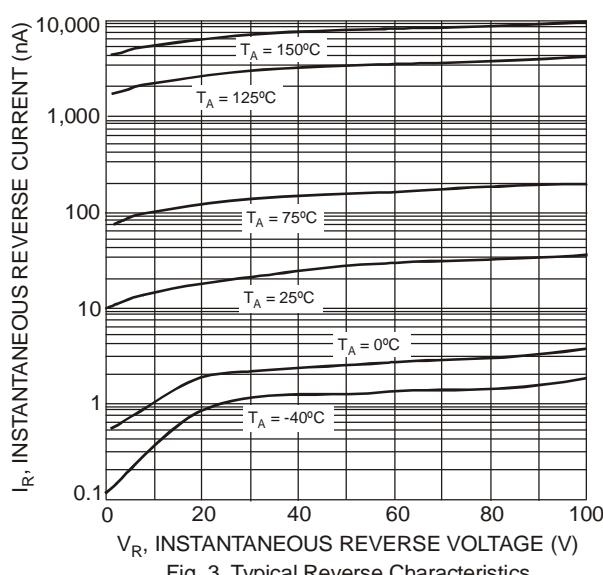
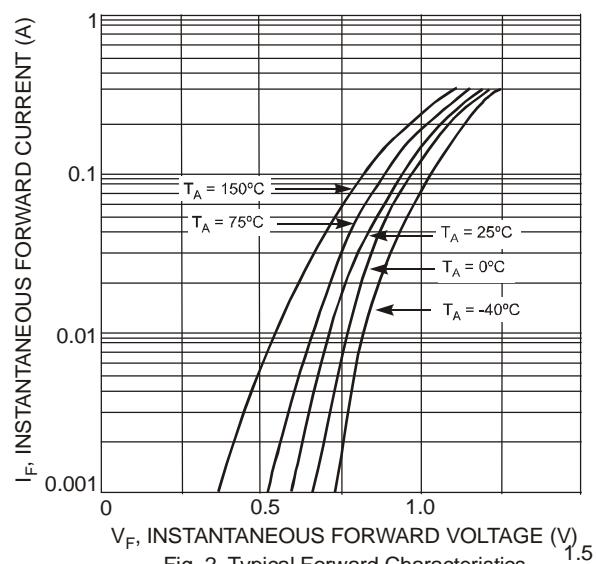
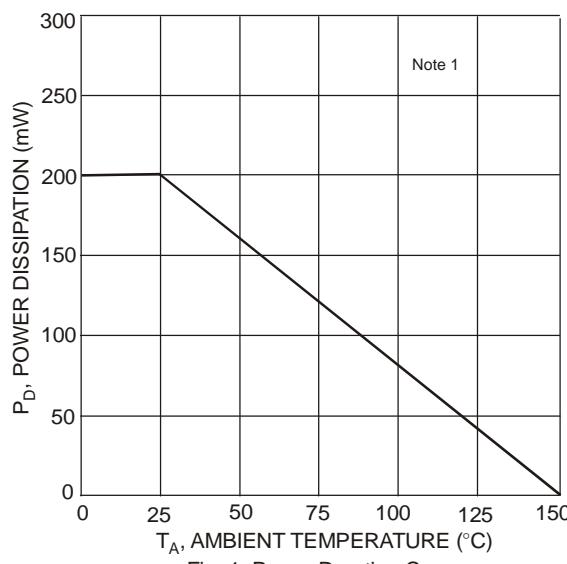
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current ($t < 1 \text{ s}, T_j = 25^\circ\text{C}$)	I_{FSM}	350	mA
Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75 \text{ V}$ at $V_R = 20 \text{ V}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R, I_F = I_R = 10 \text{ mA}, R_L = 100 \Omega$	t_{rr}	-	4	ns

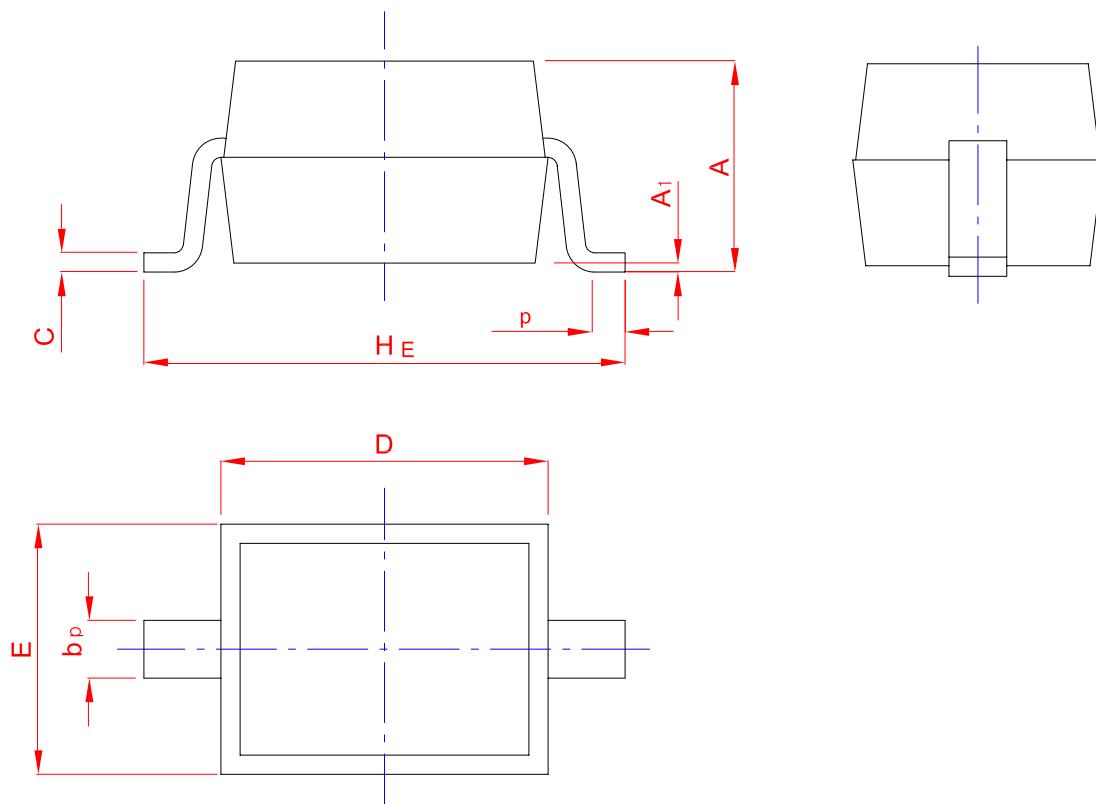
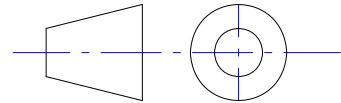
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20	0.40	0.15	1.80	1.35	2.80	0.10	0.50
	0.90	0.25	0.10	1.60	1.15	2.30	0.01	0.20